SIEMENS

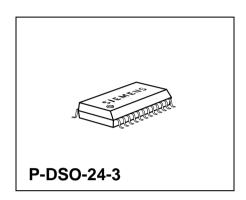
2-Phase Stepper-Motor Driver

TLE 4726

Overview Bipolar IC

Features

- 2 × 0.75 A / 50 V outputs
- Integrated driver, control logic and current control (chopper)
- Fast free-wheeling diodes
- · Low standby-current drain
- Full, half, quarter, mini step



Туре	Ordering Code	Package
TLE 4726 G	Q67006-A9297	P-DSO-24-3

Description

TLE 4726 is a bipolar, monolithic IC for driving bipolar stepper motors, DC motors and other inductive loads that operate on constant current. The control logic and power output stages for two bipolar windings are integrated on a single chip which permits switched current control of motors with 0.75 A per phase at operating voltages up to 50 V.

The direction and value of current are programmed for each phase via separate control inputs. A common oscillator generates the timing for the current control and turn-on with phase offset of the two output stages. The two output stages in a full-bridge configuration have integrated, fast free-wheeling diodes and are free of crossover current. The logic is supplied either separately with 5 V or taken from the motor supply voltage by way of a series resistor and an integrated Z-diode. The device can be driven directly by a microprocessor with the possibility of all modes from full step through half step to mini step.

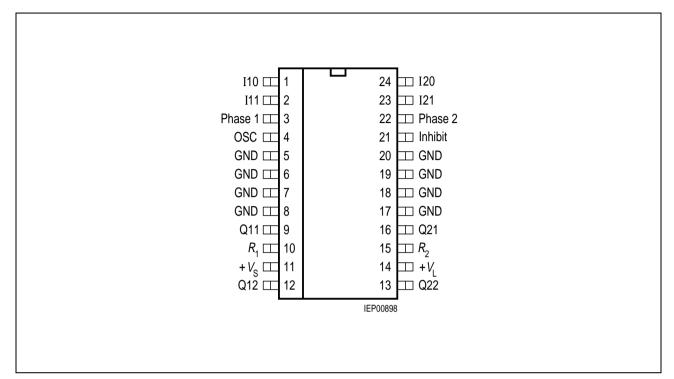


Figure 1 Pin Configuration (top view)

Pin Definitions and Functions

Pin No.	Function	on									
1, 2, 23, 24	Digital particul		_	0, IX1 for the mag	nitude of the current of the						
	IX1	IX0	Phase Current	Example of Motor Status	_						
	Н	Н	0	No current							
	Н	L	1/3 I _{max}	Hold	typical I_{max} with						
	L	Н	2/3 I _{max}	Set	$R_{\rm sense}$ = 1 Ω : 750 mA						
	L	L	I_{max}	Accelerate	_						
3	_	ntial the	phase curr		phase winding 1. On 1 to Q12, on L-potential in						
5, 6, 7, 8, 17, 18, 19, 20	Ground	Ground; all pins are connected internally.									
4	Oscilla 2.2 nF.	tor; wo	rks at appro	ox. 25 kHz if this p	in is wired to ground across						
10	Resiste	or <i>R</i> ₁ fo	r sensing th	ne current in phase	e 1.						
9, 12	Push-p diodes.		puts Q11, (Q12 for phase 1 w	ith integrated free-wheeling						
11		electrol	tic capacito	~	as possible to the IC, with a in parallel with a ceramic						
14	a series	s resisto groun	or. A Z-diod d directly or	e of approx. 7 V is	V or connect to + $V_{\rm S}$ across integrated. In both cases ble electrolytic capacitor of 100 nF.						
13, 16	Push-p diodes.		puts Q22, 0	Q21 for phase 2 w	ith integrated free-wheeling						
15	Resiste	or R_2 for	r sensing th	ne current in phase	e 2.						
21		=			by low potential on this pin. tantially.						
22	H-poter	ntial the	phase curr		This reduces the current consumption substantially. Input phase 2; controls the current flow through phase winding 2. On H-potential the phase current flows from Q21 to Q22, on L potential in the reverse direction.						

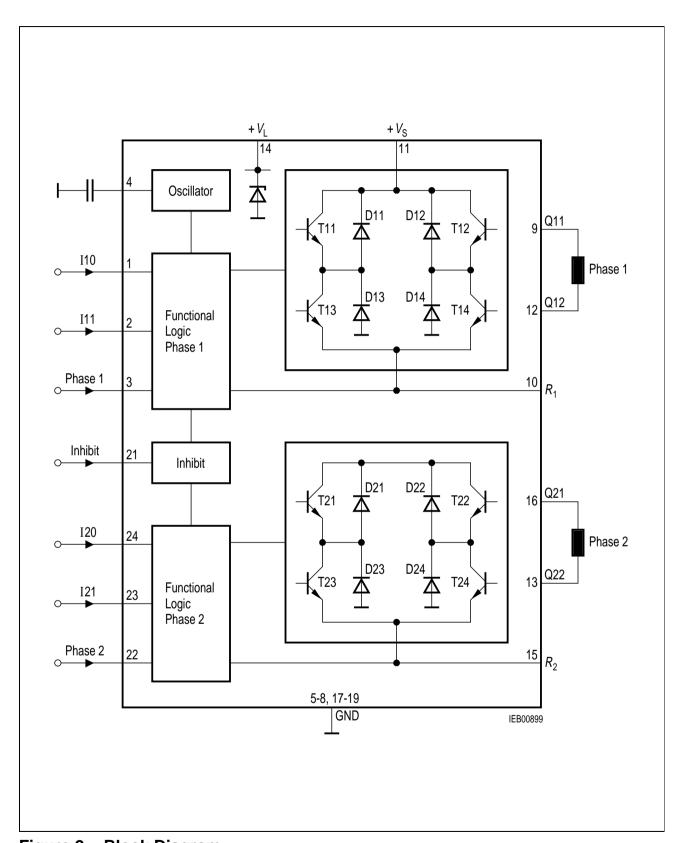


Figure 2 Block Diagram

Absolute Maximum Ratings

 $T_{\rm A}$ = - 40 to 125 $^{\circ}$ C

Parameter	Symbol	Limit Values		Unit	Remarks
		min.	max.		
Supply voltage	V_{S}	0	52	V	_
Logic supply voltage	V_{L}	0	6.5	V	Z-diode
Z-current of V_{L}	I_{L}	_	50	mA	_
Output current	I_{Q}	– 1	1	Α	_
Ground current	I_{GND}	-2	2	Α	_
Logic inputs	V_{lxx}	-6	V _L + 0.3	V	I _{XX} ; Phase 1, 2; Inhibit
R_1, R_2 , oscillator input voltage	$V_{RX,} \ V_{OSC}$	- 0.3	V _L + 0.3	V	-
Junction temperature	T_{j}		125 150	°C	– max. 1,000 h
Storage temperature	$T_{ m stg}$	- 50	125	°C	_

Operating Range

Parameter	Symbol	Limit '	Values	Unit	Remarks
		min.	max.		
Supply voltage	V_{S}	5	50	V	_
Logic supply voltage	V_{L}	4.5	6.5	V	without series resistor
Case temperature	T_{C}	- 25	110	°C	measured on pin 5 $P_{\text{diss}} = 2 \text{ W}$
Output current	I_{Q}	- 800	800	mA	_
Logic inputs	V_{IXX}	- 5	V_{L}	V	I _{XX} ; Phase 1, 2; Inhibit

Thermal Resistances

Junction ambient	R_{th}	ia –	7	75	K/W	P-DSO-24-3
Junction ambient (soldered on 35 µm thick 20 cm² PC bo	a R_{th}		5	50	K/W	P-DSO-24-3
copper area) Junction case	R_{th}	jc –	1	15	K/W	measured on pin 5 P-DSO-24-3

Characteristics

 $V_{\rm S}$ = 40 V; $V_{\rm L}$ = 5 V; - 25 °C $\leq T_{\rm j} \leq$ 125 °C Parameter Symbol Limit Values Unit Test Condition

i arameter	Symbol	_	Lillit Values		Oilit	rest condition
		min.	typ.	max.		
Current Consun	nption					
from + $V_{\rm S}$	$I_{\mathbb{S}}$	_	0.2	0.5	mA	$V_{\rm inh} = L$
from + $V_{\rm S}$	I_{S}^{S}	_	16	20	mA	$\begin{aligned} V_{\text{inh}} &= L \\ V_{\text{inh}} &= H \\ I_{\text{Q1/2}} &= 0, I_{\text{XX} = L} \\ V_{\text{inh}} &= L \\ V_{\text{inh}} &= H \\ I_{\text{Q1/2}} &= 0, I_{\text{XX} = L} \end{aligned}$
-						$I_{Q1/2} = 0, I_{XX = L}$
from + V_{L}	$ I_{L} $	_	1.7	3	mA	$V_{inh} = L$
from + V_{L}	I_{L}	_	18	25	mA	$V_{inh} = H$
						$I_{Q1/2} = 0, I_{XX = L}$

Characteristics (cont'd)

 $V_{\rm S}$ = 40 V; $V_{\rm L}$ = 5 V; - 25 °C $\leq T_{\rm j} \leq$ 125 °C

Parameter	Symbol Limit Values			Unit	Test Condition	
		min.	typ.	max.		
Oscillator		•	•		1	
Output charging current	$I_{ m OSC}$	_	110	_	μΑ	_
Charging threshold	V_{OSCL}	-	1.3	_	V	_
Discharging threshold	V_{OSCH}	_	2.3	_	V	_
Frequency	$f_{\sf OSC}$	18	25	40	kHz	C_{OSC} = 2.2 nF

Phase Current Selection Current Limit Threshold

No current	$V_{sense\;n}$	_	0	_	mV	IX0 = H; IX1 = H
Hold	$V_{\sf sense\ h}$	200	250	300	mV	IX0 = L; IX1 = H
Setpoint	$V_{sense s}$	420	540	680	mV	IX0 = H; IX1 = L
Accelerate	V_{sensea}	700	825	950	mV	IX0 = L; IX1 = L

Logic Inputs

 $(I_{X1}; I_{X0}; Phase x)$

- // //						
Threshold	V_{L}	1.4	_	2.3	V	_
		(H→L)		(L→H)		
L-input current	I_{IL}	– 10	_	_	μΑ	$V_{\rm I} = 1.4 \ { m V}$
L-input current	I_{IL}	– 100	_	_	μΑ	$V_{\rm I} = 0 \text{ V}$
H-input current	I_{IH}	_	_	10	μΑ	$V_{\rm I}$ = 5 V

Characteristics (cont'd)

 $V_{\rm S}$ = 40 V; $V_{\rm L}$ = 5 V; - 25 °C $\leq T_{\rm i} \leq$ 125 °C

Parameter	Symbol	Limit Values			Unit	Test Condition
		min.	typ.	max.		
Standby Cutout	(inhibit)					
Threshold	$V_{lnh} \ (L { ightarrow} H)$	2	3	4	V	_
Threshold	$V_{lnh} \ (H { ightarrow} L)$	1.7	2.3	2.9	V	_
Hysteresis	V_{Inhhy}	0.3	0.7	1.1	V	_

7.4

6.5

٧

 $I_1 = 50 \text{ mA}$

8.2

Power Outputs

Z-voltage

Diode Transistor Sink Pair (D13, T13; D14, T14; D23, T23; D24, T24)

 V_{LZ}

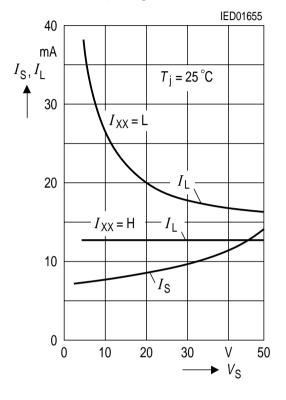
Saturation voltage	V_{satl}	_	0.3	0.6	V	$I_{\rm Q} = -0.5 {\rm A}$
Saturation voltage	V_{satl}	_	0.5	1	V	$I_{\rm Q} = -0.75 {\rm A}$
Reverse current	I_{RI}	_	_	300	μΑ	$V_{\rm Q}$ = 40 V
Forward voltage	V_{FI}	_	0.9	1.3	V	$I_{\rm Q} = 0.5 {\rm A}$
Forward voltage	V_{FI}	_	1	1.4	V	$I_{\rm Q} = 0.75 {\rm A}$

Diode Transistor Source Pair

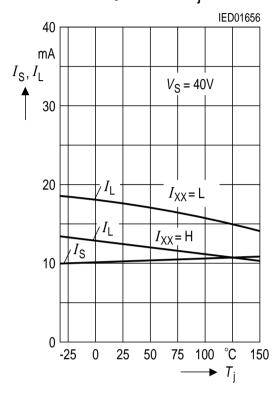
(D11, T11; D12, T12; D21, T21; D22, T22)

Saturation voltage	V_{satuC}	_	0.9	1.2	V	$I_{\rm Q} = 0.5 \text{ A};$
						charge
Saturation voltage	V_{satuD}	_	0.3	0.7	V	$I_{\rm Q} = 0.5 \mathrm{A};$
Coturation valtage	17		4.4	4 4		discharge
Saturation voltage	V_{satuC}	_	1.1	1.4	V	$I_{\rm Q} = 0.75 {\rm A};$
						charge
Saturation voltage	V_{satuD}	_	0.5	1	V	$I_{\rm Q} = 0.75 {\rm A};$
						discharge
Reverse current	I_{Ru}	_	_	300	μΑ	$V_{Q} = 0 \text{ V}$
Forward voltage	V_{Fu}	_	1	1.3	V	$I_{\rm Q} = -0.5 {\rm A}$
Forward voltage	V_{Fu}	_	1.1	1.4	V	$I_{\rm O} = -0.75 {\rm A}$
Diode leakage current	I_{SL}	_	1	2	mΑ	$I_{\rm F} = -0.75 {\rm A}$

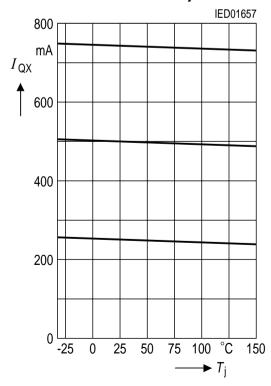
Quiescent Current $I_{\rm S}, I_{\rm L}$ versus Supply Voltage $V_{\rm S}$



Quiescent Current I_{S} , I_{L} versus Junction Temperature T_{i}



Output Current I_{QX} versus Junction Temperature T_i



Operating Condition:

 $V_{\rm L} = 5 \, {\rm V}$ $V_{\rm Inh} = {\rm H}$

 $C_{\rm OSC}$ = 2.2 nF

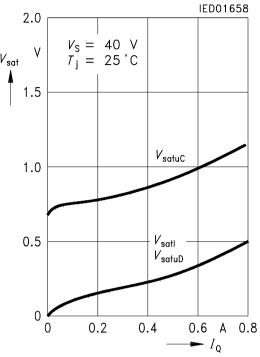
 $R_{\rm sense} = 1 \,\Omega$

Load: L = 10 mH

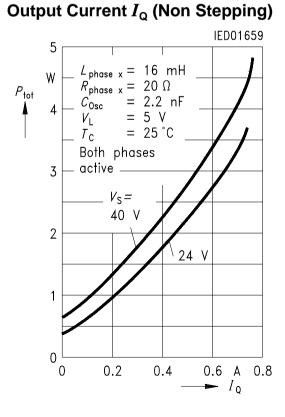
 $R = 2.4 \Omega$ = 50 Hz

 $f_{\text{phase}} = 50 \text{ Hz}$ mode: fullstep

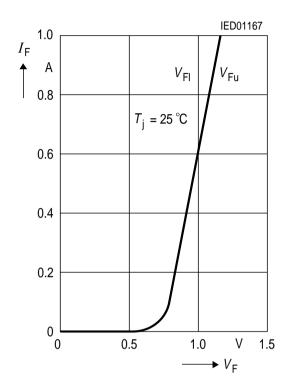
Output Saturation Voltages V_{sat} versus Output Current I_{Q}



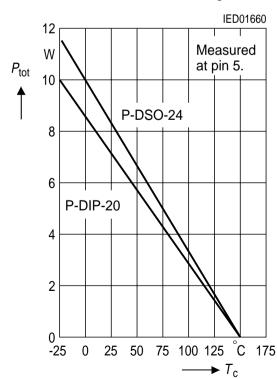
Typical Power Dissipation P_{tot} versus



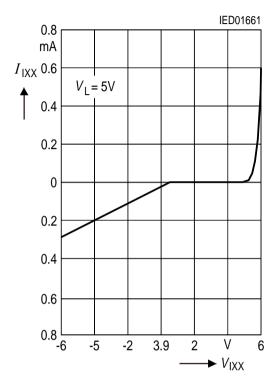
Forward Current $I_{\rm F}$ of Free-Wheeling Diodes versus Forward Voltages $V_{\rm F}$



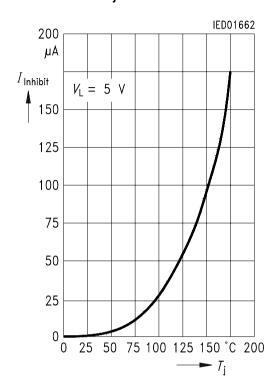
Permissible Power Dissipation P_{tot} versus Case Temperature T_{C}



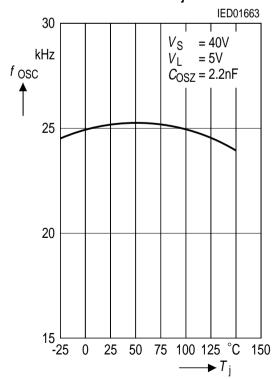
Input Characteristics of $I_{\rm xx}$, Phase X, Inhibit



Input Current of Inhibit versus Junction Temperature $T_{\rm i}$



Oscillator Frequency $f_{\rm OSC}$ versus Junction Temperature $T_{\rm j}$



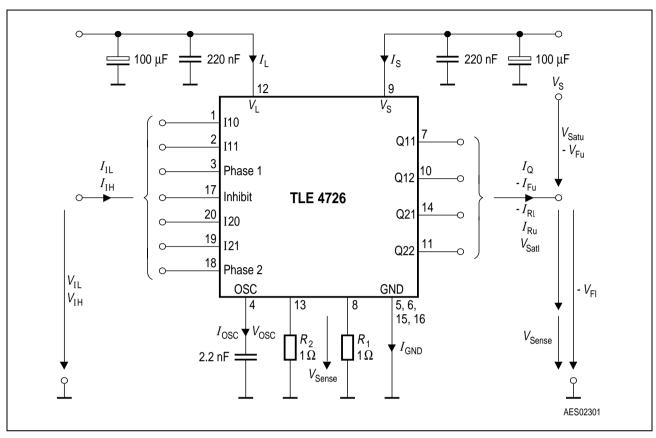


Figure 3 Test Circuit

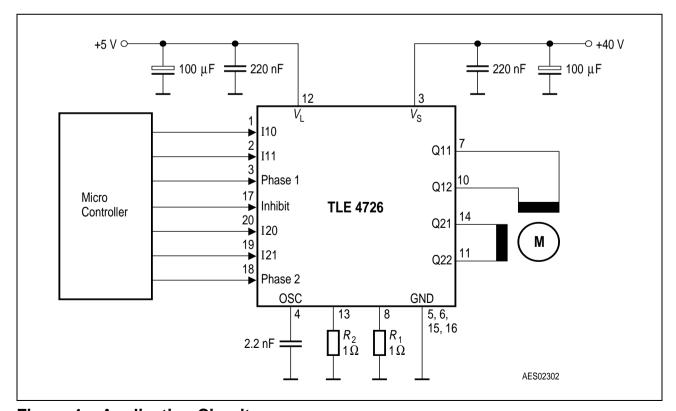


Figure 4 Application Circuit

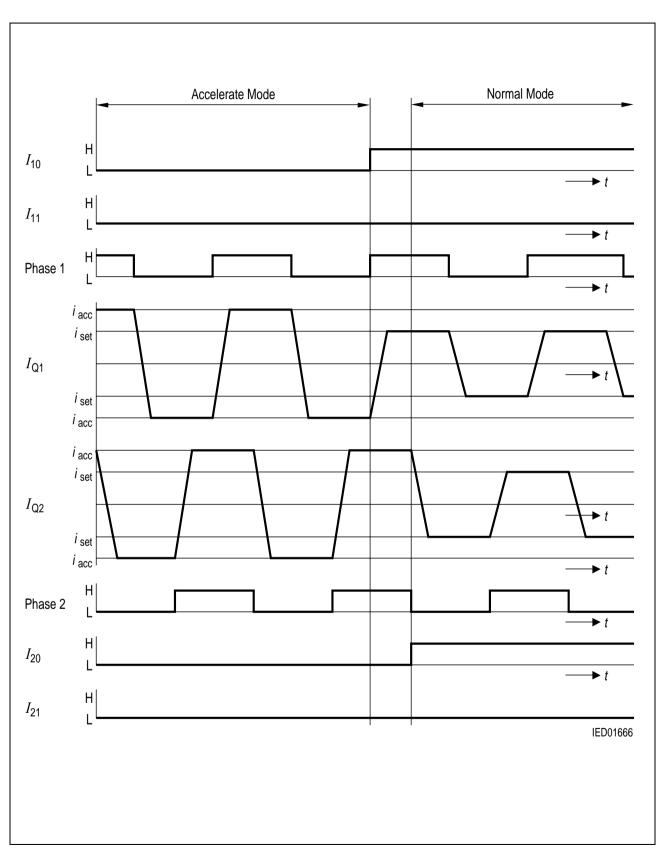


Figure 5 Full-Step Operation

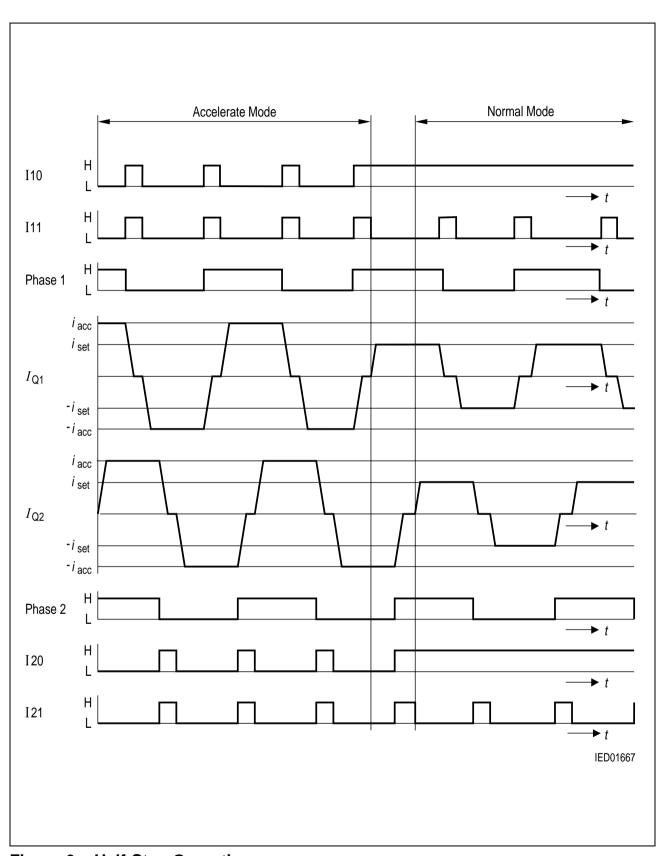


Figure 6 Half-Step Operation

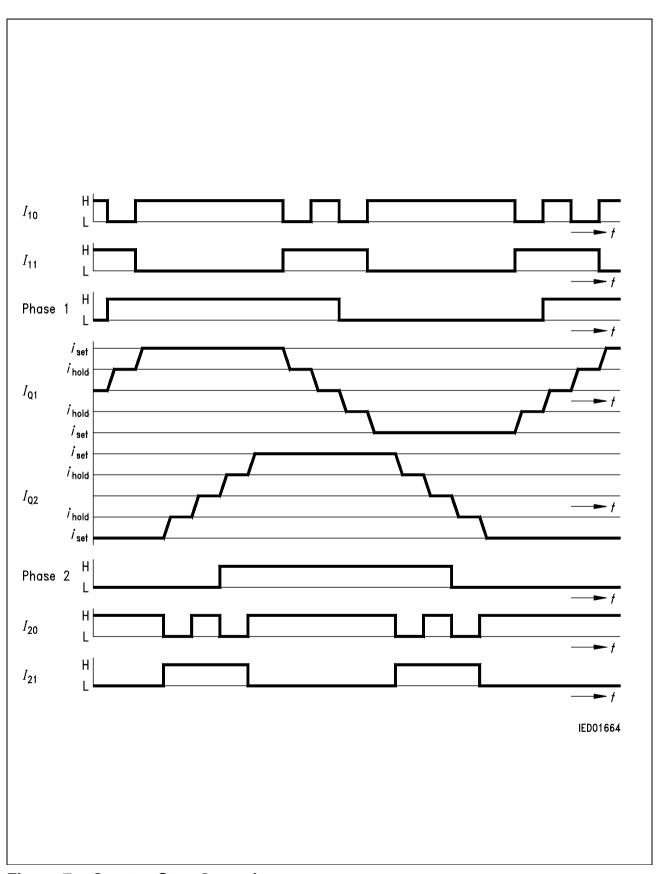


Figure 7 Quarter-Step Operation

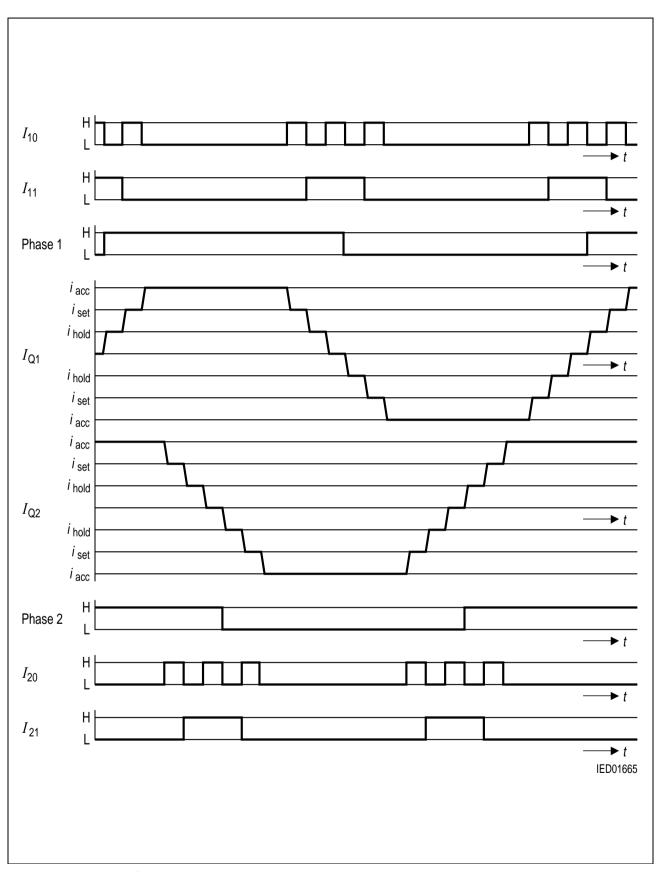


Figure 8 Mini-Step Operation

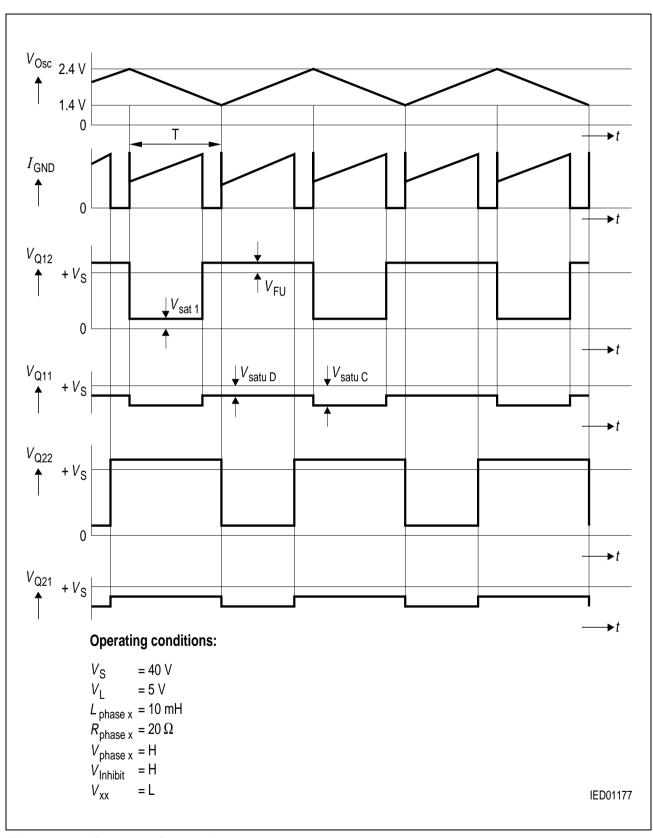


Figure 9 Current Control

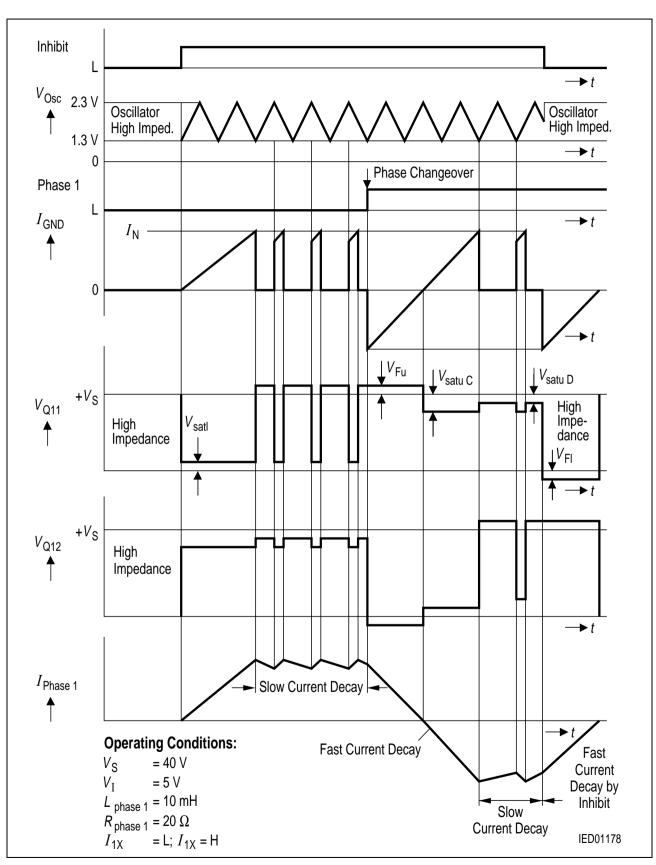


Figure 10 Phase Reversal and Inhibit

Calculation of Power Dissipation

The total power dissipation P_{tot} is made up of

saturation losses P_{sat} (transistor saturation voltage and diode forward voltages), **quiescent losses** P_{q} (quiescent current times supply voltage) and **switching losses** P_{s} (turn-ON / turn-OFF operations).

The following equations give the power dissipation for chopper operation without phase reversal. This is the worst case, because full current flows for the entire time and switching losses occur in addition.

$$\begin{split} P_{\text{tot}} &= 2 \times P_{\text{sat}} + P_{\text{q}} + 2 \times P_{\text{s}} \\ \text{where} \qquad P_{\text{sat}} &\cong I_{\text{N}} \left\{ \left. V_{\text{satI}} \times d + V_{\text{Fu}} \left(1 - d \right) + V_{\text{satuC}} \times d + V_{\text{satuD}} \left(1 - d \right) \right. \right\} \\ P_{\text{q}} &= I_{\text{q}} \times V_{\text{S}} + I_{\text{L}} \times V_{\text{L}} \\ P_{\text{S}} &\cong \frac{V_{\text{S}}}{T} \left\{ \frac{i_{\text{D}} \times t_{\text{DON}}}{2} + \frac{i_{\text{D}} + i_{\text{R}} \times t_{\text{ON}}}{4} + \frac{I_{\text{N}}}{2} t_{\text{DOFF}} + t_{\text{OFF}} \right\} \end{split}$$

 $I_{\rm N}$ = nominal current (mean value)

 $I_{\rm g}$ = quiescent current

 $i_{\rm D}$ = reverse current during turn-on delay

 $i_{\rm P}$ = peak reverse current

 $t_{\rm p}$ = conducting time of chopper transistor

 t_{ON} = turn-ON time t_{OFF} = turn-OFF time t_{DON} = turn-ON delay t_{DOFF} = turn-OFF delay T = cycle duration d = duty cycle t_{p}/T

 V_{satl} = saturation voltage of sink transistor (T3, T4)

 $V_{
m satuC}$ = saturation voltage of source transistor (T1, T2) during charge cycle $V_{
m satuD}$ = saturation voltage of source transistor (T1, T2) during discharge cycle

 V_{Fu} = forward voltage of free-wheeling diode (D1, D2)

 $egin{array}{ll} V_{
m S} &= {
m supply \ voltage} \ V_{
m L} &= {
m logic \ supply \ voltage} \ I_{
m L} &= {
m current \ from \ logic \ supply} \ \end{array}$

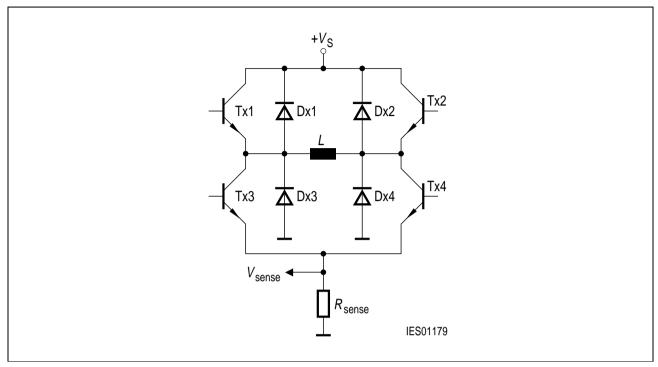


Figure 11

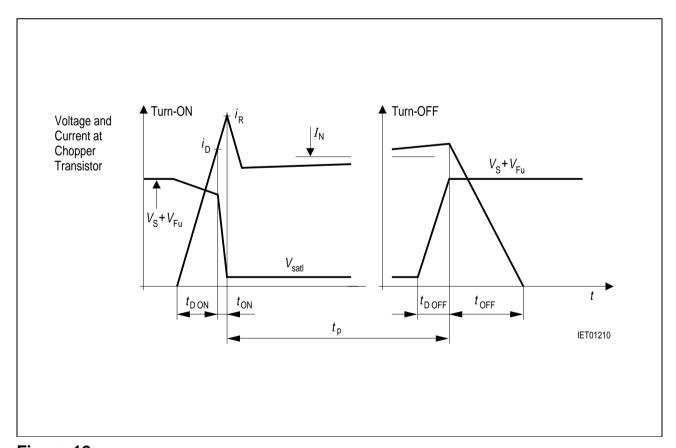


Figure 12

Application Hints

The TLE 4726 is intended to drive both phases of a stepper motor. Special care has been taken to provide high efficiency, robustness and to minimize external components.

Power Supply

The TLE 4726 will work with supply voltages ranging from 5 V to 50 V at pin $V_{\rm S}$. As the circuit operates with chopper regulation of the current, interference generation problems can arise in some applications. Therefore the power supply should be decoupled by a 0.22 μF ceramic capacitor located near the package. Unstabilized supplies may even afford higher capacities.

Current Sensing

The current in the windings of the stepper motor is sensed by the voltage drop across R_1 and R_2 . Depending on the selected current internal comparators will turn off the sink transistor as soon as the voltage drop reaches certain thresholds (typical 0 V, 0.25 V, 0.5 V and 0.75 V); (R_1 , R_2 = 1 Ω). These thresholds are neither affected by variations of $V_{\rm L}$ nor by variations of $V_{\rm S}$.

Due to chopper control fast current rises (up to $10 \text{ A/}\mu\text{s}$) will occur at the sensing resistors R_1 and R_2 . To prevent malfunction of the current sensing mechanism R_1 and R_2 should be pure ohmic. The resistors should be wired to GND as directly as possible. Capacitive loads such as long cables (with high wire to wire capacity) to the motor should be avoided for the same reason.

Synchronizing Several Choppers

In some applications synchrone chopping of several stepper motor drivers may be desireable to reduce acoustic interference. This can be done by forcing the oscillator of the TLE 4726 by a pulse generator overdriving the oscillator loading currents (approximately Š \pm 100 μ A). In these applications low level should be between 0 V and 1 V while high level should be between 2.6 V and V_{L} .

Optimizing Noise Immunity

Unused inputs should always be wired to proper voltage levels in order to obtain highest possible noise immunity.

To prevent crossconduction of the output stages the TLE 4726 uses a special break before make timing of the power transistors. This timing circuit can be triggered by short glitches (some hundred nanoseconds) at the Phase inputs causing the output stage to become high resistive during some microseconds. This will lead to a fast current decay during that time. To achieve maximum current accuracy such glitches at the Phase inputs should be avoided by proper control signals.

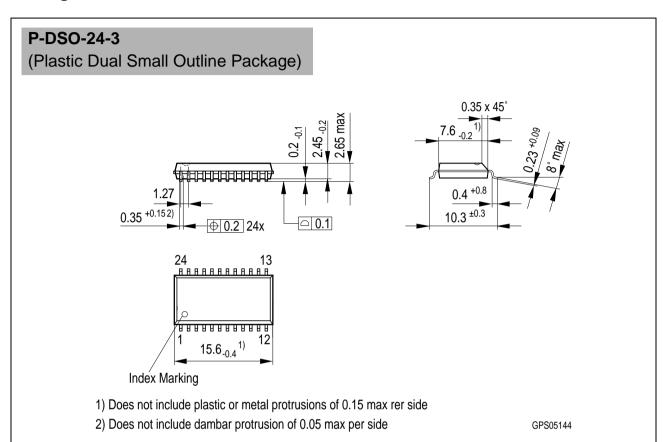
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Thermal Shut Down

To protect the circuit against thermal destruction, thermal shut down has been implemented. To provide a warning in critical applications, the current of the sensing element is wired to input Inhibit. Before thermal shut down occurs Inhibit will start to pull down by some hundred microamperes. This current can be sensed to build a temperature prealarm.

1998-02-01

Package Outlines



Sorts of Packing

Package outlines for tubes, trays etc. are contained in our Data Book "Package Information".

SMD = Surface Mounted Device

Dimensions in mm